## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

GATE ELECTRODE FORMING METHODS USING CONDUCTIVE HARD MASK

Application Number:

Confirmation Number:

First Named Applicant:

Oleg Gluschenkov

Attorney Docket Number:

FIS920040196US1

Art Unit:

Examiner:

Search string:

( 6693333 or 6664153 or 6633497 or 6448590 or 6441447 or 6426301 or 6204073

or 20030109121 or 20030153139 or 20020196647 or 20020177279 or

20030104663 ).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
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WL	2	6664153	2003-12-16	ANG, ET AL.	1		
WLL	3	6633497	2003-10-14	NICKEL			
CULL	4	6448590	2002-09-10	ADKISSON, ET AL.			
INL	5	6441447	2002-08-27	CZAGAS, ET AL.			
W	6	6426301	2002-07-30	SHIELDS, ET AL.			
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## **US Published Applications**

Note: Applicant is not required to submit a paper copy of cited US Published Applications

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WILL	3	20020196647	2002-12-26	NICKEL				
WU	4	20020177279	2002-11-28	ADKISSON, ET AL.				

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W4		6,340,629	1/22/02	YEO, E	<del></del>		+		<b>\</b>	
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Patent and Trademark Office \* U.S. DEPARTMENT OF COMMERCE

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